



SEMiX® 3p

Trench IGBT Modules

SEMiX303GB12E4p

Features*

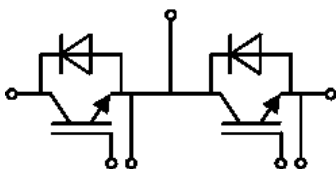
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- Press-fit pins as auxiliary contacts
- UL recognized, file no. E63532

Typical Applications

- AC inverter drives
- UPS
- Renewable energy systems

Remarks

- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- V_{isol} between temperature sensor and power section is only 2500V
- For storage and case temperature with TIM see document "TP(*) SEMiX 3p"



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _c	T _j = 175 °C	T _c = 25 °C	469	A
		T _c = 80 °C	361	A
I _{Cnom}			300	A
I _{CRM}			900	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C
Inverse diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	T _j = 175 °C	T _c = 25 °C	371	A
		T _c = 80 °C	278	A
I _{FRM}			600	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1485	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			600	A
T _{stg}	module without TIM		-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.80	2.05	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.80	0.90	V
		$T_j = 150^\circ\text{C}$	0.70	0.80	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	3.3	3.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	5.0	5.3	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 11.4\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_j = 25^\circ\text{C}$			4.0	mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	18.5		nF
C_{oes}		$f = 1\text{ MHz}$	1.22		nF
C_{res}		$f = 1\text{ MHz}$	1.04		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		1695		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		2.5		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	180		ns
t_r	$I_C = 300\text{ A}$	$T_j = 150^\circ\text{C}$	55		ns
E_{on}	$V_{GE} = +15/-15\text{ V}$ $R_{G on} = 1.3\text{ }\Omega$	$T_j = 150^\circ\text{C}$	23		mJ
$t_{d(off)}$	$R_{G off} = 1.3\text{ }\Omega$	$T_j = 150^\circ\text{C}$	470		ns
t_f	$di/dt_{on} = 5600\text{ A}/\mu\text{s}$ $di/dt_{off} = 2400\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	110		ns
E_{off}	$dv/dt = 3500\text{ V}/\mu\text{s}$ $L_s = 21\text{ nH}$	$T_j = 150^\circ\text{C}$	38		mJ
$R_{th(j-c)}$	per IGBT			0.094	K/W
$R_{th(c-s)}$	per IGBT ($\lambda_{grease} = 0.81\text{ W}/(\text{m}^2\text{K})$)		0.03		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material		0.021		K/W



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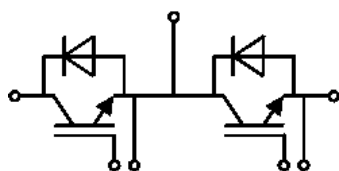
Typical Applications

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- UPS
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Remarks

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Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.16	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		3.0	3.4	mΩ
		T _j = 150 °C		4.2	4.6	mΩ
I _{RRM}	I _F = 300 A	T _j = 150 °C		330		A
Q _{rr}	di/dt _{off} = 6000 A/μs	T _j = 150 °C		50		μC
E _{rr}	V _{GE} = -15 V	T _j = 150 °C		23		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.155	K/W
R _{th(c-s)}	per diode (λ _{grease} =0.81 W/(m²K))			0.046		K/W
R _{th(c-s)}	per diode, pre-applied phase change material			0.037		K/W
Module						
L _{CE}				20		nH
R _{CC'+EE'}	measured per switch	T _C = 25 °C		1.2		mΩ
		T _C = 125 °C		1.65		mΩ
R _{th(c-s)1}	calculated without thermal coupling			0.009		K/W
R _{th(c-s)2}	including thermal coupling, T _s underneath module (λ _{grease} =0.81 W/(m²K))			0.014		K/W
R _{th(c-s)2}	including thermal coupling, T _s underneath module, pre-applied phase change material			0.010		K/W
M _s	to heat sink (M5)		3		6	Nm
M _t		to terminals (M6)	3		6	Nm
						Nm
w					350	g
Temperature Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



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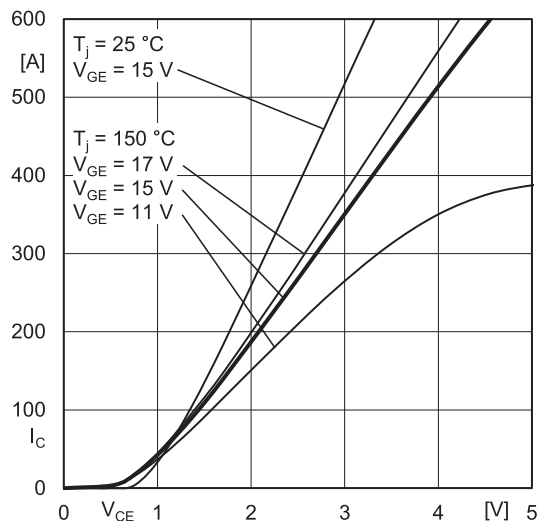
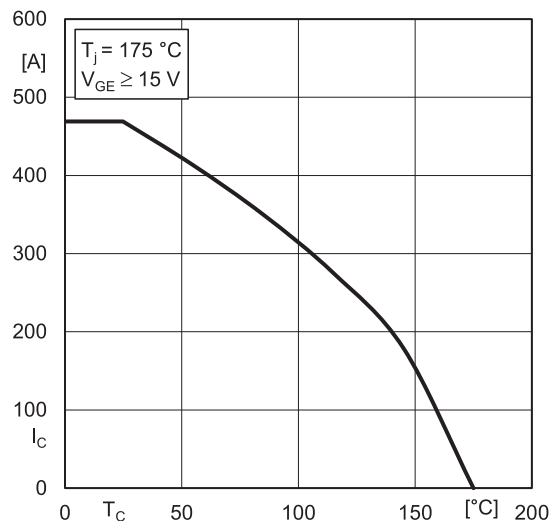
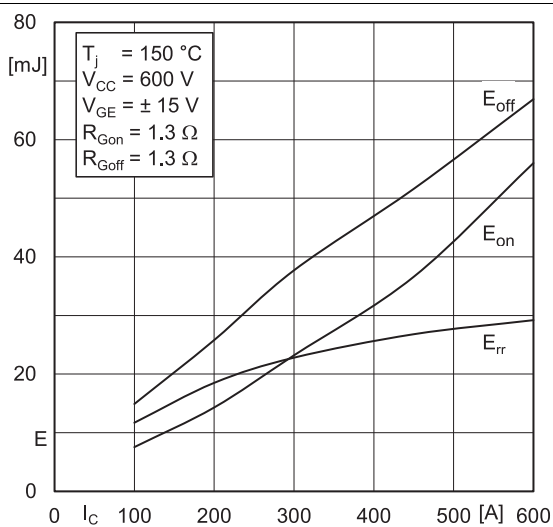
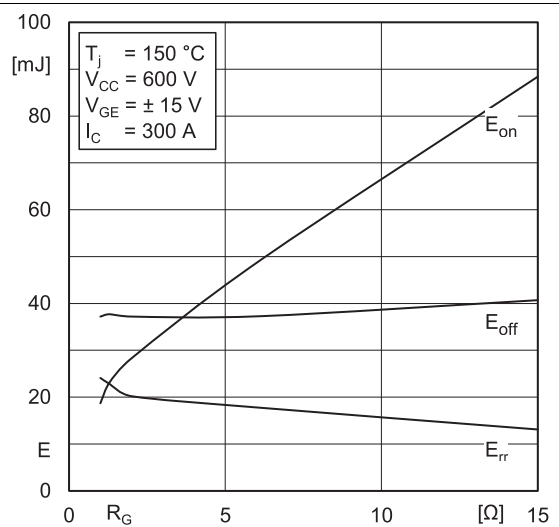
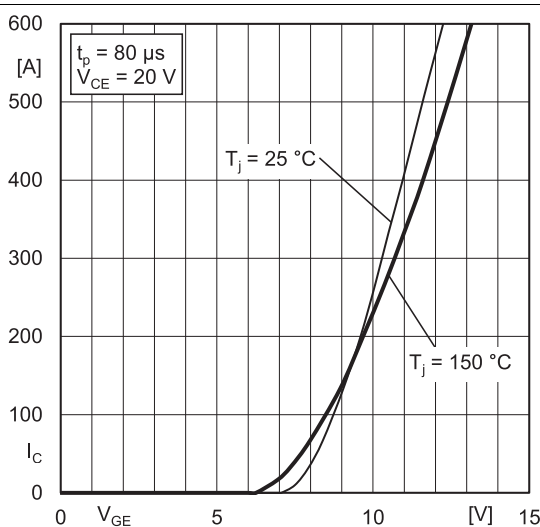
Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + EE'$ Fig. 2: Rated current vs. temperature $I_C = f(T_C)$ Fig. 3: Typ. turn-on /-off energy = $f(I_C)$ Fig. 4: Typ. turn-on /-off energy = $f(R_G)$ 

Fig. 5: Typ. transfer characteristic

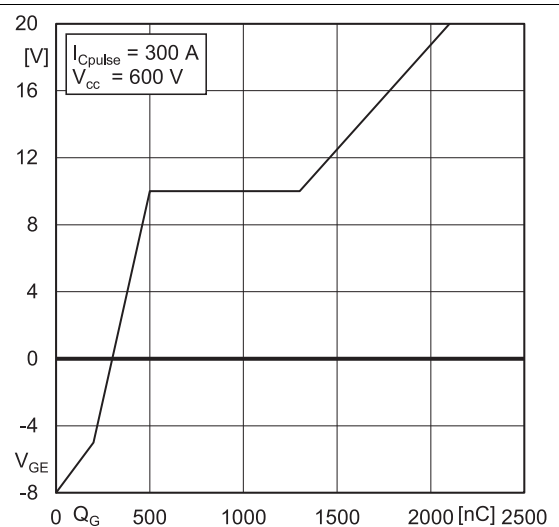


Fig. 6: Typ. gate charge characteristic

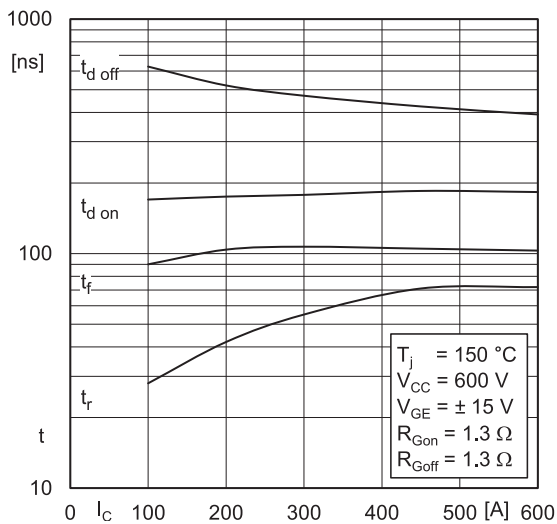


Fig. 7: Typ. switching times vs. I_C

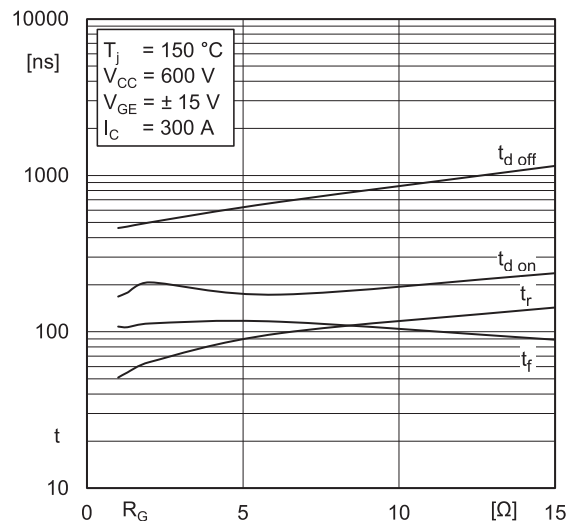


Fig. 8: Typ. switching times vs. gate resistor R_G

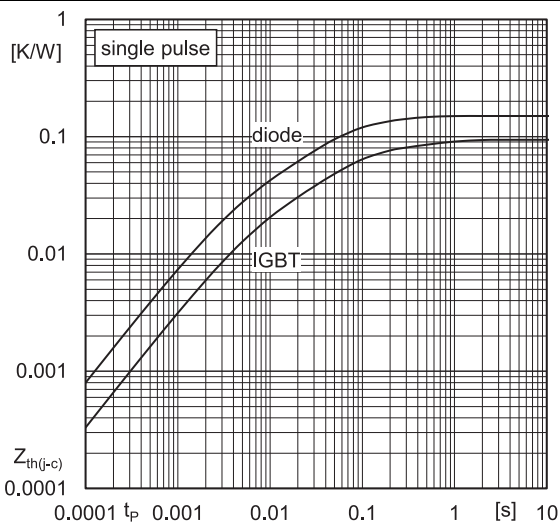


Fig. 9: Transient thermal impedance

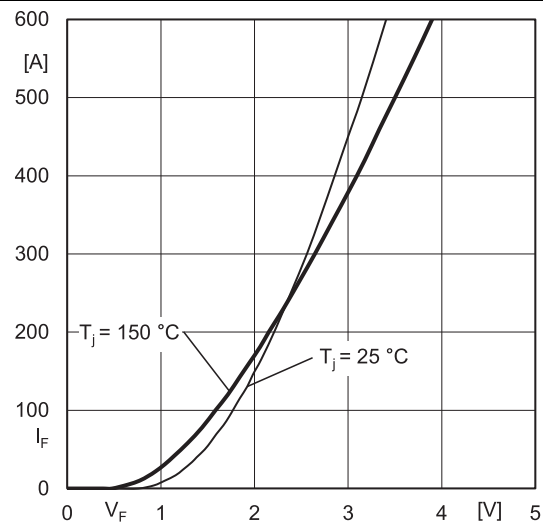


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

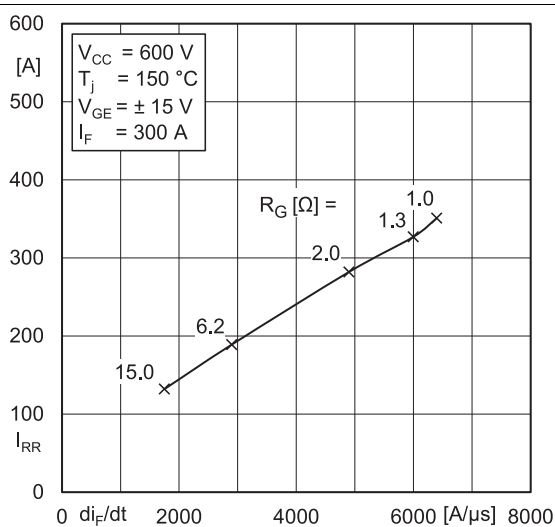


Fig. 11: Typ. CAL diode peak reverse recovery current

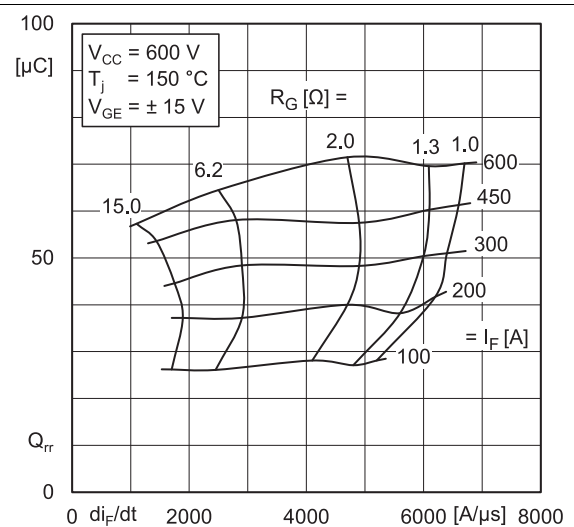


Fig. 12: Typ. CAL diode recovery charge

	0,3 connector 3-4/10-11	
	0,2 each single connector	A



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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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